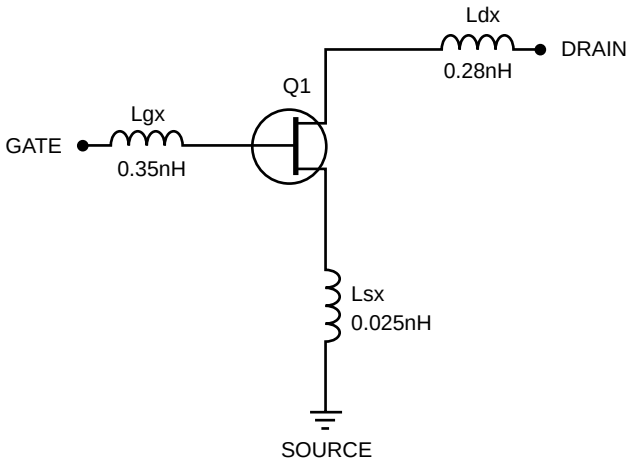
NEC

NONLINEAR MODEL | NE32900

SCHEMATIC



FET NONLINEAR MODEL PARAMETERS (1)

Parameters	Q1	Parameters	Q1
VTO	-0.825	RG	7
VTOSC	0	RD	4
ALPHA	7	RS	4
BETA	0.148	RGMET	0
GAMMA	0.081	KF	0
GAMMADC	0.05	AF	1
Q	2.5	TNOM	27
DELTA	0.7	XTI	3
VBI	0.6	EG	1.43
IS	1e-14	VTOTC	0
N	1	BETATCE	0
RIS	0	FFE	1
RID	0		
TAU	3e-12		
CDS	0.095e-12		
RDB	5000		
CBS	1e-9		
CGSO	0.42e-12		
CGDO	0.023e-12		
DELTA1	0.3		
DELTA2	0.6		
FC	0.5		
VBR	Infinity		

(1) Series IV Libra TOM Model

UNITS

Parameter	Units
time	seconds
capacitance	farads
inductance	henries
resistance	ohms
voltage	volts
current	amps

MODEL RANGE

Frequency: 0.5 to 26.5 GHz

Bias: V_{DS} = 1 V to 3 V, I_D = 5 mA to 25 mA

I_{DSS} = 54.3 mA @ V_{GS} = 0, V_{DS} = 2 V

Date: 1/98

EXCLUSIVE NORTH AMERICAN AGENT FOR NEC RF, MICROWAVE & OPTOELECTRONIC SEMICONDUCTORS

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